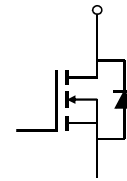


100V 2.8m N-Ch Power MOSFET

Features

Product Summary

Parameter	Value	Unit
$V_{DS}$	100	V
$V_{GS(th)}_{Typ}$	2.7	V
$I_D$ (@ $V_{GS} = 10V$ ) <sup>(1)</sup>	196	A
$R_{DS(ON)}_{Typ}$ (@ $V_{GS} = 10V$ )	2.8	m



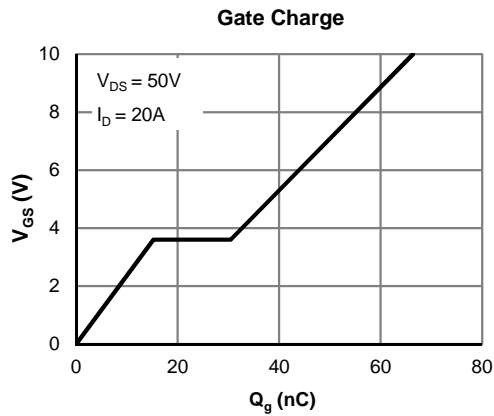
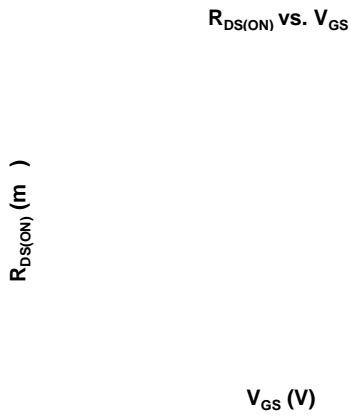
Rev. 1.1

Ordering Information

Device	Package	# of Pins	Marking	MSL	$T_J$ (°C)	Media	Quantity (pcs)
JMSH1003AE7Q-13	TO-263-7L	7	SH1003AQ	1	-55 to 175	13-inch Reel	800

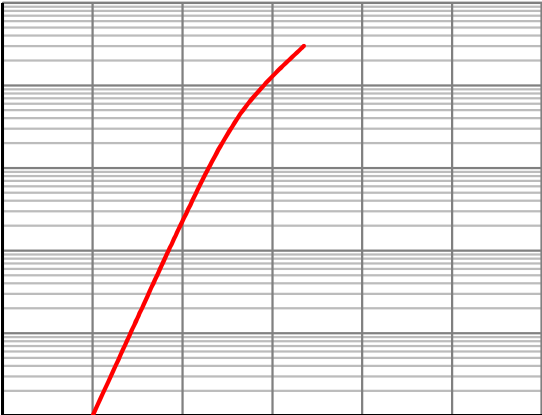
Absolute Maximum Ratings (@  $T_A = 25^\circ C$  unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	100	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V
			A
	$I_{DM}$		A
Avalanche Current <sup>(3)</sup>	$I_{AS}$	52	A
Avalanche Energy <sup>(3)</sup>	$E_{AS}$	406	mJ
Power Dissipation <sup>(4)</sup>	$P_D$	283	W
		142	W
Junction & Storage Temperature Range	$T_J, T_{STG}$	-55 to 175	°C



	Symbol	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	$V_{(BR)DSS}$	100			V
				1.0	
				5.0	
	$I_{GSS}$			±100	nA
	$V_{GS(th)}$	2.0	2.7	4.0	V
	$R_{DS(on)}$		2.8	3.5	m
	$g_{FS}$		85		S
	$V_{SD}$		0.71	1.0	V
	$I_S$			283	A
	$C_{iss}$		4398		pF
	$C_{oss}$		1361		pF
	$C_{rss}$		8.5		pF
	$R_g$		2.5		
	$Q_g$		66		nC
	$Q_g$		44		nC
	$Q_{gs}$		15.2		nC
	$Q_{gd}$		15.2		nC
	$t_{D(on)}$		17.2		ns
	t				

Typical Electrical & Thermal Characteristics





**Typical Electrical & Thermal Characteristics**

---

---

---

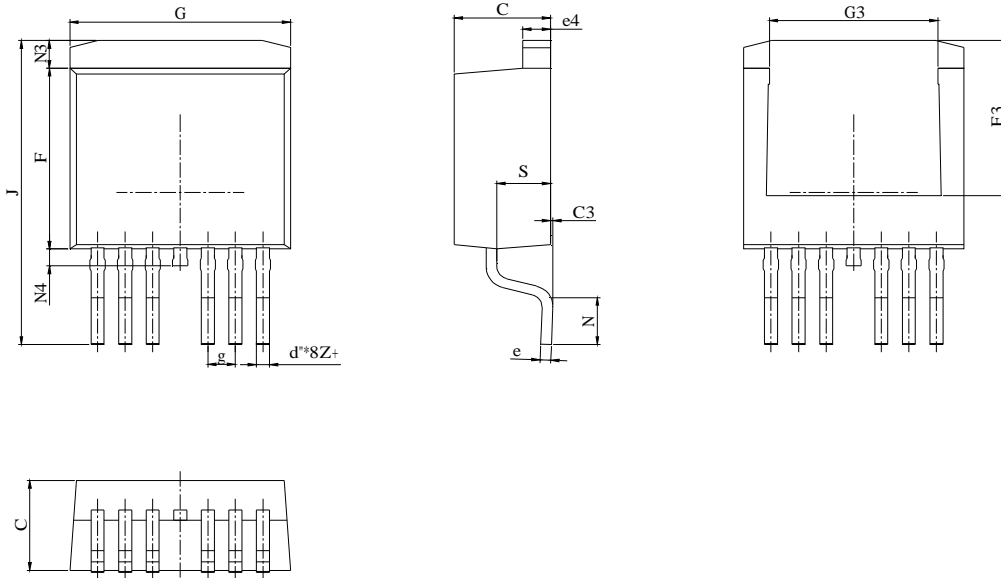
---

---



TO-263-7L Package Information

Package Outline



FKO	OINNIOGVGT		
	OKP	PQO	OCZ
C	6046	6066	6086
C3	2022	2032	2047
d	2072	2082	2092
e	2062	2072	2082
e4	3037	3049	3062
F	:0:4	:0:4	:024
F3	9087TGH		
G	:0:8	32038	32058
G3	80:2	90:2	:022
g	3049DUE		
J	36083	37022	370:
N	309:	4054	40:2
N3		3058TGH	
N4		3042TGH	
N5		2047DUE	
S	4052	406:	4092

